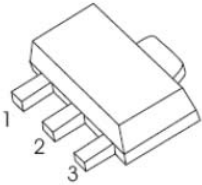
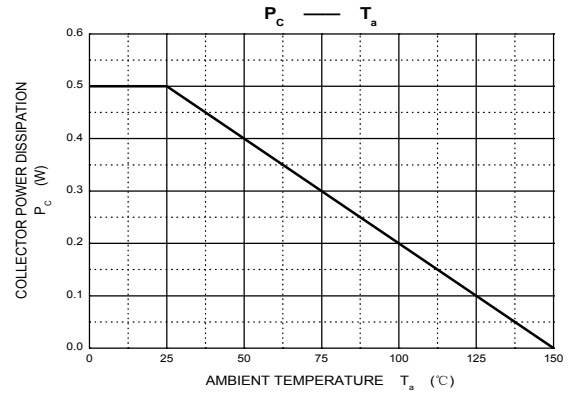
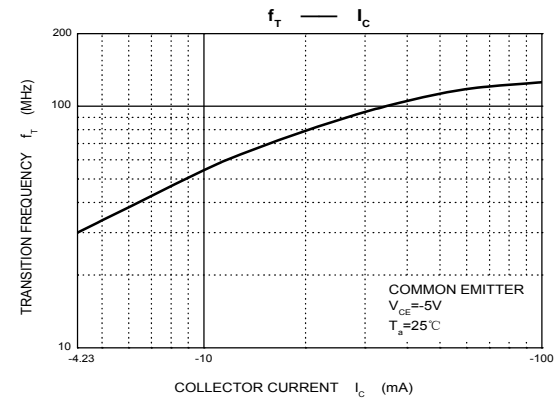
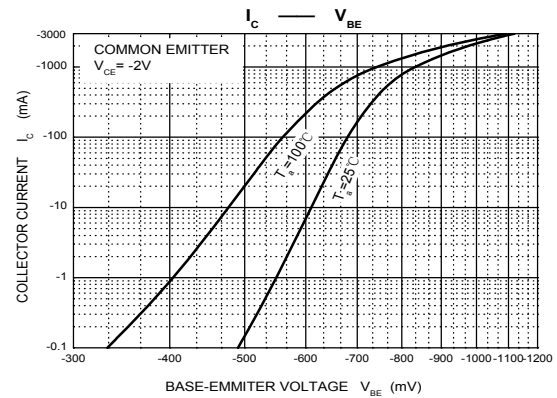
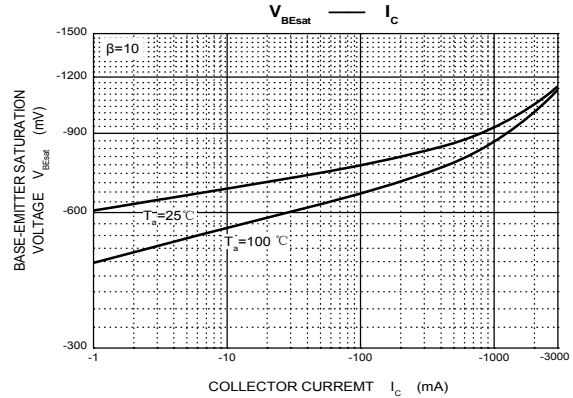
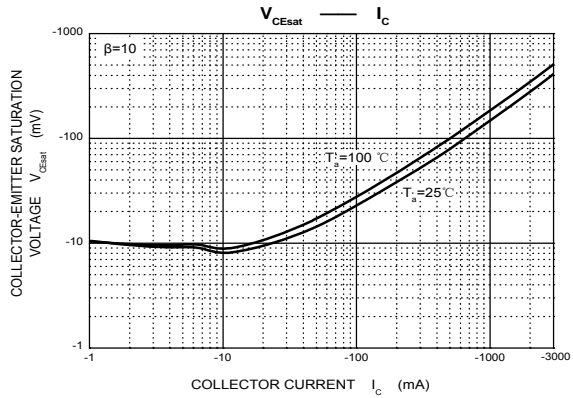
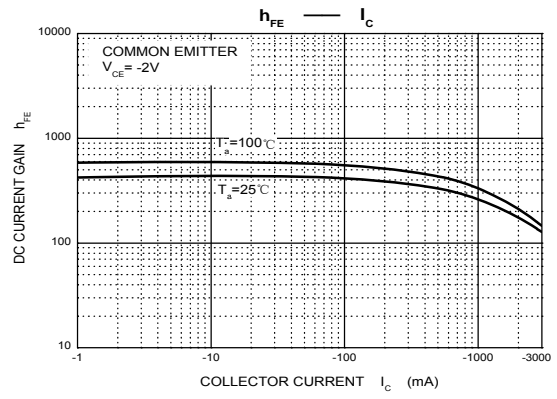
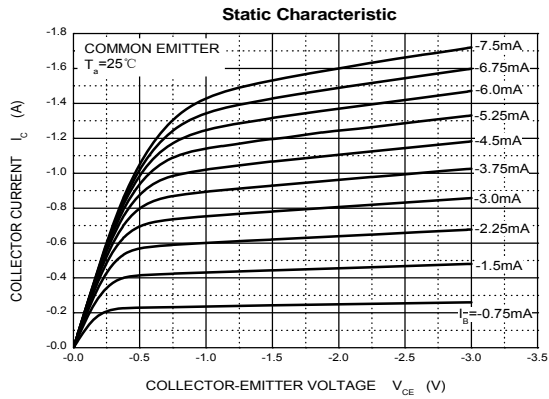


TRANSISTOR (PNP)	SOT-89-3L Plastic-Encapsulate Transistors					
SOT-89	Features					
	Low speed switching					
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)						
Symbol	Parameter	Value	Unit			
V _{CB0}	Collector-Base Voltage	-40	V			
V _{CEO}	Collector-Emitter Voltage	-30	V			
V _{EBO}	Emitter-Base Voltage	-6	V			
I _C	Collector Current -Continuous	-3	A			
P _C	Collector Power Dissipation	0.5	W			
R _{θJA}	Thermal Resistance, Junction to Ambient	250	°C/W			
T _J	Junction Temperature	150	°C			
T _{stg}	Storage Temperature	-55~150	°C			
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)						
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} = -40V, I _E =0			-1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-30V, I _B =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-1	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -1A	60		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B = -0.2A			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-2A, I _B = -0.2A			-1.5	V
Transition frequency	f _T	V _{CE} = -5V, I _C =-0.1A f =10MHz	50			MHz
CLASSIFICATION OF h_{FE}						
Rank	R	O	Y	GR		
Range	60-120	100-200	160-320	200-400		

Typical Characteristics



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)